

## **Ultra Small ESD Protector**



# Description

The SES5VD923-2U ESD protector is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. The SES5VD923-2U protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. The SES5VD923-2U is available in a SOD-923 package with working voltages of 5 volt. It gives designer the flexibility to protect one unidirectional line in applications where arrays are not practical. Additionally, it may be "sprinkled" around the board in applications where board space is at a premium. It may be used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 ( $\pm$ 15kV air,  $\pm$ 8kV contact discharge)





## Feature

- 100 Watts peak pulse power (tp = 8/20 µ s)
- Transient protection for data lines to

IEC 61000-4-2 (ESD)  $\pm$ 25kV (air),  $\pm$ 10kV (contact)

IEC 61000-4-4 (EFT) 40A (5/50ns)

IEC 61000-4-5 (Lightning) 24A (8/20 μ s)

- Small package for use in portable electronics
- Suitable replacement for MLV's in ESD protection applications
- Protect one I/O or power line
- Low clamping voltage
- Stand off voltages: 5V
- Low leakage current
- Solid-state silicon-avalanche technology
- Small Body Outline Dimensions: 0.8mm×0.6mm×0.5mm
- Equivalent to 0402 package

## **Applications**

- Cell Phone Handsets and Accessories
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Cordless Phones
- Digital Cameras
- Peripherals
- MP3 Players

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## SES5VD923-2U

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## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Working Voltage	$V_{RWM}$				5	V
Breakdown voltage	$V_{BR}$	I <sub>t</sub> =1mA	6	6.8	7.2	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> =5V T=25℃		0.005	1	μΑ
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =10mA		0.8		V
Clamping Voltage	V <sub>C</sub>	$I_{PP}=5A$ $t_{P}=8/20\mu S$			9.8	V
Clamping Voltage	Vc	I <sub>PP</sub> =16A t <sub>P</sub> = 8/20μS			12.5	V
Junction Capacitance	C <sub>j</sub>	V <sub>R</sub> =0V f = 1MHz 40		55	pF	
Junction Capacitance	C <sub>j</sub>	V <sub>R</sub> =2.5V f = 1MHz		30	40	pF

## Absolute maximum rating @25℃

Rating	Symbol	Value	Units
Peak Pulse Power ( t <sub>P</sub> = 8/20μS )	P <sub>pp</sub>	100	W
Maximum Peak Pulse Current ( $t_P = 8/20\mu S$ )	I <sub>pp</sub>	16	А
Lead Soldering Temperature	T <sub>L</sub>	260 (10 sec)	°C
Operating Temperature	TJ	-55 to +125	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

# Applications Information

#### Device Connection Options

SES5VD923-2U is designed to protect one data, I/O, or power supply line. The device is unidirectional and may be used on lines where the signal polarity is above ground. The cathode dot should be placed towards the line that is to be protected.

#### ■ Circuit Board Layout Recommendations for Suppression of ESD.

Good circuit board layout is critical for the suppression of ESD induced transients. The following guidelines are recommended:

Place the TVS near the input terminals or connectors to restrict transient coupling.

Minimize the path length between the TVS and the protected line.

Minimize all conductive loops including power and ground loops.

The ESD transient return path to ground should be kept as short as possible.

Never run critical signals near board edges.

Use ground planes whenever possible. for multilayer printed-circuit boards, use ground vias.

Keep parallel signal paths to a minimum.

Avoid running protection conductors in parallel with unprotected conductor.

Minimize all printed-circuit board conductive loops including power and ground loops.

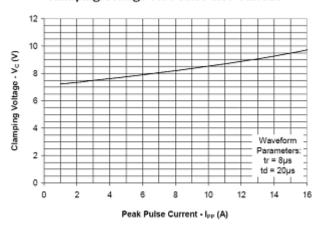
Avoid using shared transient return paths to a common ground point.



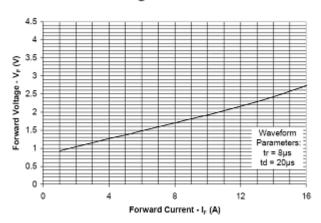


# **Typical Characteristics**

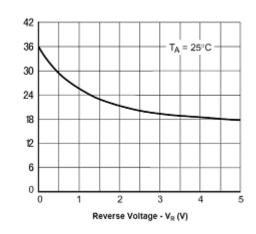
### Clamping Voltage vs. Peak Pulse Current



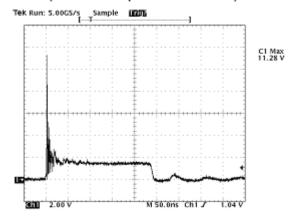
### Forward Voltage vs. Forward Current



#### Junction Capacitance vs. Reverse Voltage



ESD Clamping (8kV Contact per IEC 61000-4-2)

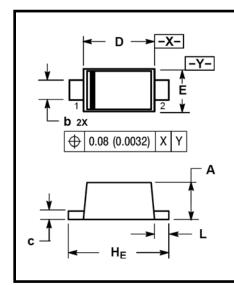


Capacitance · C<sub>j</sub> (pF)

SES5VD923-2U

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# **Product dimension**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF

BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.36	0.40	0.43	0.014	0.016	0.017
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	0.95	1.00	1.05	0.037	0.039	0.041
L	0.05	0.10	0.15	0.002	0.004	0.006

# **Revision History**

Revision	Date	Changes
1.0	2008-7-3	-

Website: http://www.semiteltech.com

For additional information, please contact your local Sales Representative.

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